Product data sheet

# 1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

### 2. Features and benefits

- · Low reverse recovery current and low thermal resistance
- Reduces switching losses in associated MOSFET

# 3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies
- · Half-bridge lighting ballasts

## 4. Quick reference data

Table 1. Quick reference data

| Symbol             | Parameter                       | Conditions  | Min | Тур | Max  | Unit |
|--------------------|---------------------------------|---|-----|-----|------|------|
| $V_R$              | reverse voltage                 | DC  | -   | -   | 600  | V    |
| I <sub>F(AV)</sub> | average forward current         | $δ = 0.5$ ; $T_{mb} \le 103$ °C; SQW; <u>Fig. 1</u> ;<br><u>Fig. 2</u>  | -   | -   | 8    | A    |
| I <sub>FRM</sub>   | repetitive peak forward current | $δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 103 °C$ ; SQW  | -   | -   | 16   | A    |
| I <sub>FSM</sub>   | non-repetitive peak             | $t_p = 8.3 \text{ ms}; T_{j(init)} = 150 \text{ °C}; SIN$   | -   | -   | 60   | Α    |
|                    | forward current                 | t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 150 °C; SIN  | -   | -   | 55   | Α    |
| Static characte    | eristics                        |   |     |     |      |      |
| V <sub>F</sub>     | forward voltage                 | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C  | -   | 2   | 2.9  | V    |
|                    |                                 | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>  | -   | 1.5 | 1.85 | V    |
| Dynamic chara      | acteristics                     |   |     |     |      |      |
| t <sub>rr</sub>    | reverse recovery time           | $I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 50 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$       | -   | 30  | 52   | ns   |
|                    |                                 | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$<br>$T_j = 100 ^{\circ}\text{C}$  | -   | 32  | 40   | ns   |
|                    |                                 | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 5$ | -   | 20  | -    | ns   |

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# 5. Pinning information

### **Table 2. Pinning information**

| Pin | Symbol | Description                         | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|--------------------|----------------|
| 1   | K      | cathode                             | mb                 | к <b>—</b> А   |
| 2   | А      | anode                               | <b>├</b>           | 001aaa020      |
| mb  | mb     | mounting base; connected to cathode | TO-220AC (SOD59)   |                |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number | Package  |  |         |  |  |  |  |
|-------------|----------|--|---------|--|--|--|--|
|             | Name     | Description  | Version |  |  |  |  |
| BYC8D-600   | TO-220AC | plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC | SOD59   |  |  |  |  |

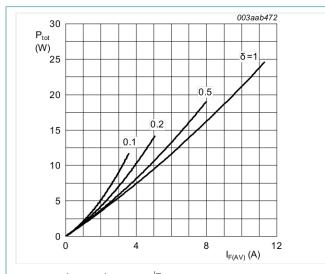
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# 7. Limiting values

## **Table 4. Limiting values**

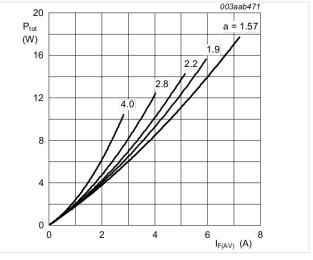
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                       | Conditions   | Min | Max | Unit |
|--------------------|---------------------------------|--|-----|-----|------|
| $V_{RRM}$          | repetitive peak reverse voltage |  | -   | 600 | V    |
| $V_{RWM}$          | crest working reverse voltage   |  | -   | 600 | V    |
| $V_R$              | reverse voltage                 | DC   | -   | 600 | V    |
| I <sub>F(AV)</sub> | average forward current         | $δ = 0.5$ ; $T_{mb} \le 103$ °C; SQW; <u>Fig. 1</u> ;<br><u>Fig. 2</u> | -   | 8   | А    |
| I <sub>FRM</sub>   | repetitive peak forward current | $\delta$ = 0.5; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 103 °C; SQW  | -   | 16  | Α    |
| I <sub>FSM</sub>   | non-repetitive peak             | $t_p = 8.3 \text{ ms; } T_{j(init)} = 150 \text{ °C; SIN}$             | -   | 60  | Α    |
|                    | forward current                 | t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 150 °C; SIN             | -   | 55  | Α    |
| T <sub>stg</sub>   | storage temperature             |  | -40 | 150 | °C   |
| Tj                 | junction temperature            |  | -   | 150 | °C   |



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)} / I_{F(AV)}$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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## 8. Thermal characteristics

#### **Table 5. Thermal characteristics**

| Symbol                | Parameter  | Conditions  | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base    | Fig. 3      | -   | -   | 2.5 | K/W  |
| $R_{th(j-a)}$         | thermal resistance<br>from junction to<br>ambient free air | in free air | -   | 60  | -   | K/W  |

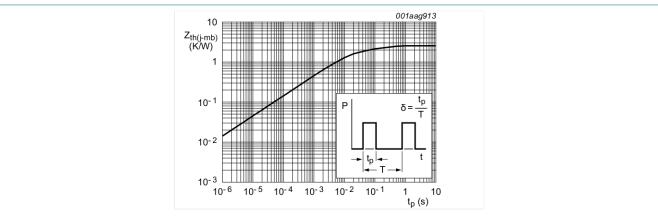


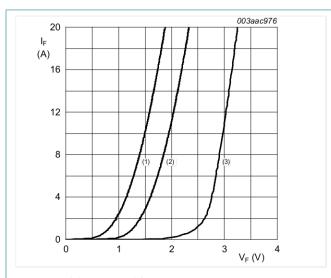
Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

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### 9. Characteristics

#### **Table 6. Characteristics**

| Symbol          | Parameter                     | Conditions  | Min | Тур | Max  | Unit |
|-----------------|-------------------------------|---|-----|-----|------|------|
| Static chara    | acteristics                   |   |     |     |      |      |
| V <sub>F</sub>  | forward voltage               | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C  | -   | 2   | 2.9  | V    |
|                 |                               | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>  | -   | 1.5 | 1.85 | V    |
| I <sub>R</sub>  | reverse current               | V <sub>R</sub> = 600 V; Tj = 25 °C  | -   | 9   | 40   | μΑ   |
|                 |                               | V <sub>R</sub> = 500 V; T <sub>j</sub> = 100 °C   | -   | 1.1 | 3    | mA   |
| Dynamic ch      | aracteristics                 |   |     |     |      |      |
| t <sub>rr</sub> | reverse recovery time         | $I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 50 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$       | -   | 30  | 52   | ns   |
|                 |                               | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$<br>$T_j = 100 \text{ °C}$        | -   | 32  | 40   | ns   |
|                 |                               | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 5$ | -   | 20  | -    | ns   |
| I <sub>RM</sub> | peak reverse recovery current | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$<br>$T_j = 125 \text{ °C}$         | -   | 1.5 | 5.5  | А    |
|                 |                               | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$<br>$T_j = 100 \text{ °C}$        | -   | 9.5 | 12   | А    |
| Q <sub>r</sub>  | recovered charge              | $I_F = 1 \text{ A}$ ; $V_R = 100 \text{ V}$ ; $dI_F/dt = 100 \text{ A}/\mu\text{s}$ ; $T_j = 25 \text{ °C}$     | -   | 13  | -    | nC   |
| $V_{FR}$        | forward recovery voltage      | $I_F = 10 \text{ A}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 6                   | -   | 8   | 10   | V    |



(1)  $T_j$  = 150 °C; typical values

(2)  $T_j = 150$  °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values



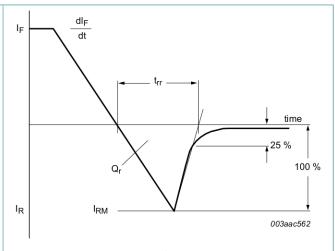
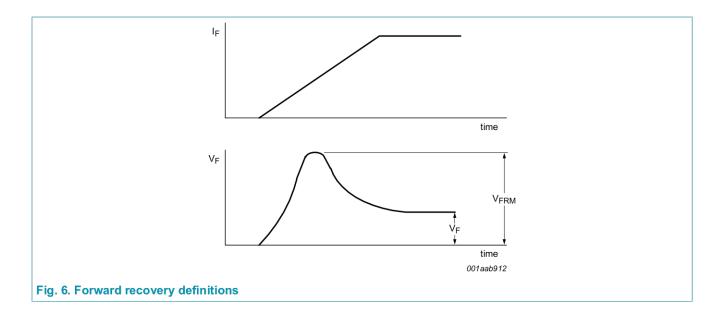


Fig. 5. Reverse recovery definitions; ramp recovery

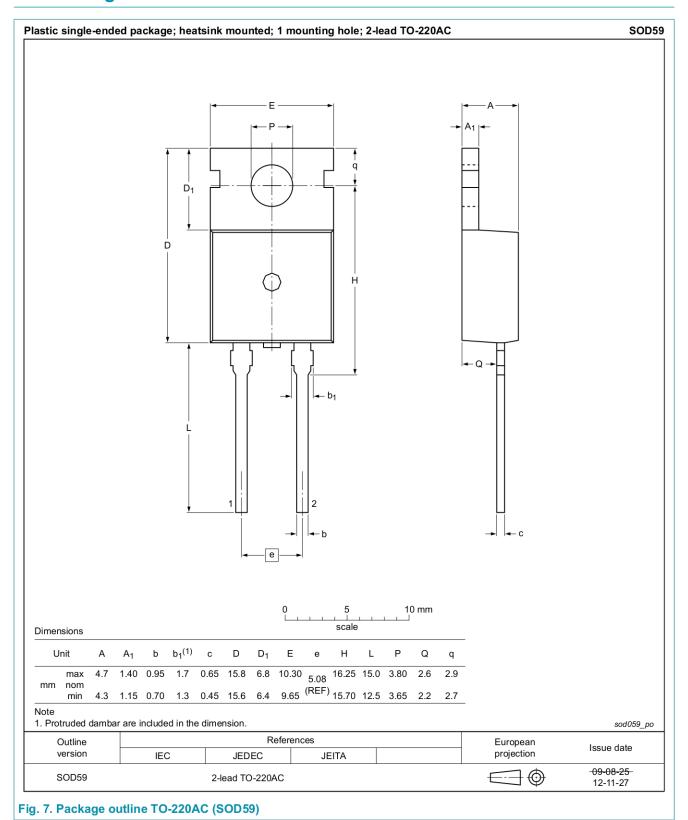
## Hyperfast power diode



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# 10. Package outline



### Hyperfast power diode

## 11. Legal information

#### **Data sheet status**

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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**BYC8D-600** 

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